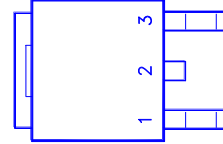
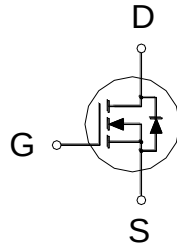


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
100V	105m Ω	15A



1: GATE
2: DRAIN
3: SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	15	A
	$T_C = 100^\circ\text{C}$		9.2	
Pulsed Drain Current ¹		I_{DM}	45	
Avalanche Current		I_{AS}	5.4	
Avalanche Energy	$L = 1\text{mH}$	E_{AS}	14.8	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	50	W
	$T_C = 100^\circ\text{C}$		20	
Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		62.5	$^\circ\text{C} / \text{W}$
Junction-to-Case	$R_{\theta JC}$		2.5	

¹Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

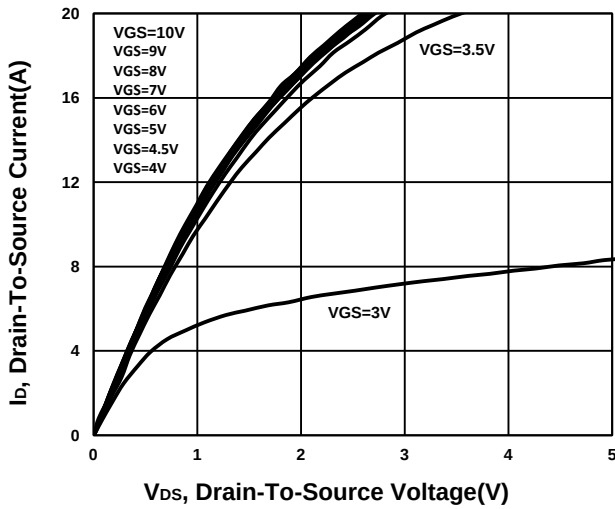
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.8	3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80V, V_{GS} = 0V$			1	μA
		$V_{DS} = 80V, V_{GS} = 0V, T_J = 125^\circ C$			10	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 6A$		81	120	$m\Omega$
		$V_{GS} = 10V, I_D = 6A$		77	105	

Forward Transconductance ¹	g _{fs}	V _{DS} = 10V, I _D = 6A		20		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	473	592	710	pF
Output Capacitance	C _{oss}		41	52	62	
Reverse Transfer Capacitance	C _{rss}		18	30	42	
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz	0.7	1.3	2	Ω
Total Gate Charge ²	Q _{g(VGS=10V)}	V _{DS} = 50V , I _D =6A	11	13.9	16.7	nC
	Q _{g(VGS=4.5V)}		6.4	8	9.6	
Gate-Source Charge ²	Q _{gs}		1.6	2	2.4	
Gate-Drain Charge ²	Q _{gd}		2.8	4.7	6.6	
Turn-On Delay Time ²	t _{d(on)}	V _{DS} = 50V , I _D ≅ 6A, V _{GS} = 10V, R _{GEN} =6 Ω		18		nS
Rise Time ²	t _r			15		
Turn-Off Delay Time ²	t _{d(off)}			51		
Fall Time ²	t _f			15		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _J = 25 ° C)						
Continuous Current	I _S				15	A
Forward Voltage ¹	V _{SD}	I _F = 6A, V _{GS} = 0V			1.4	V
Diode Reverse Recovery Time	t _{rr}	I _F = 6A, dI/dt=100A/μs	12.5	25	50	nS
Diode Reverse Recovery Charge	Q _{rr}		12.5	25	50	nC

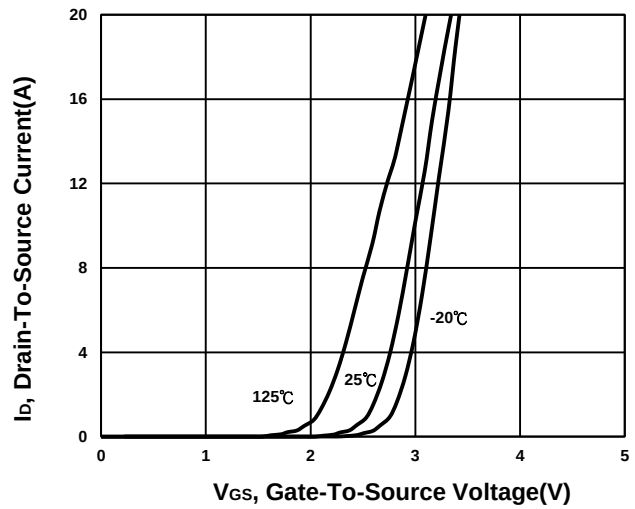
¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

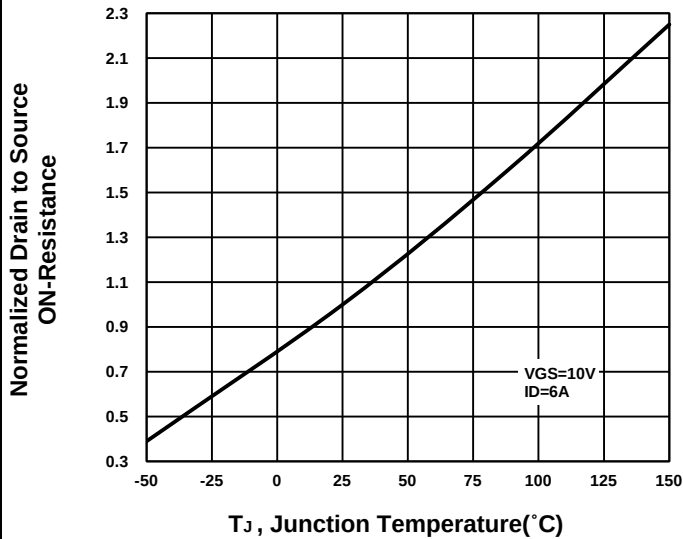
Output Characteristics



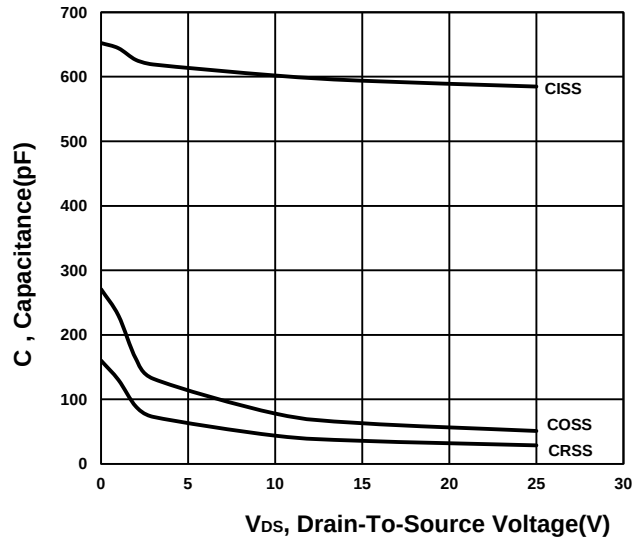
Transfer Characteristics



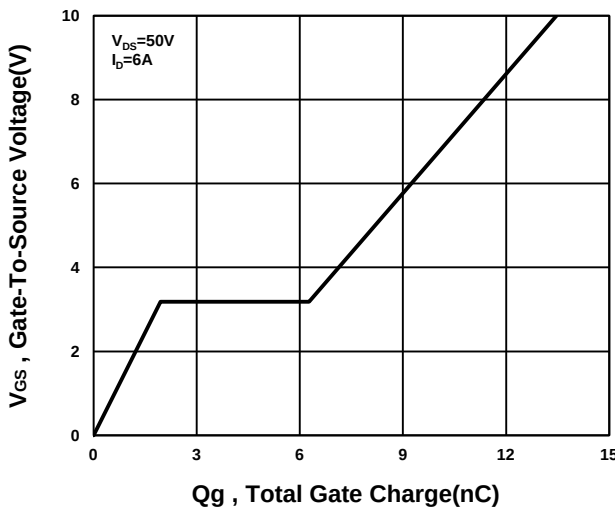
On-Resistance VS Temperature



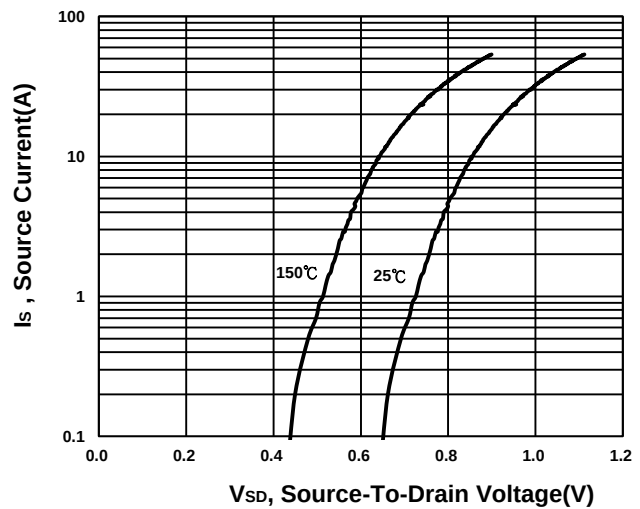
Capacitance Characteristic



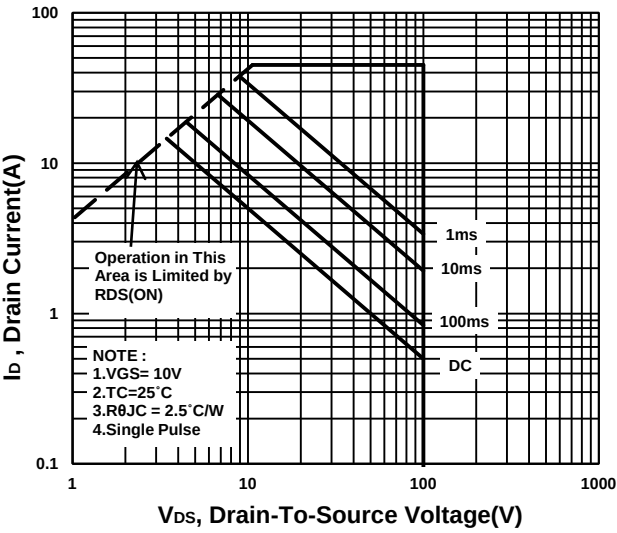
Gate charge Characteristics



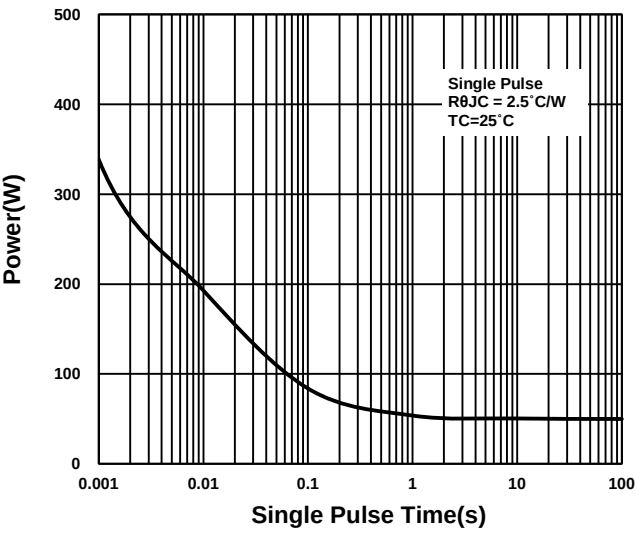
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

